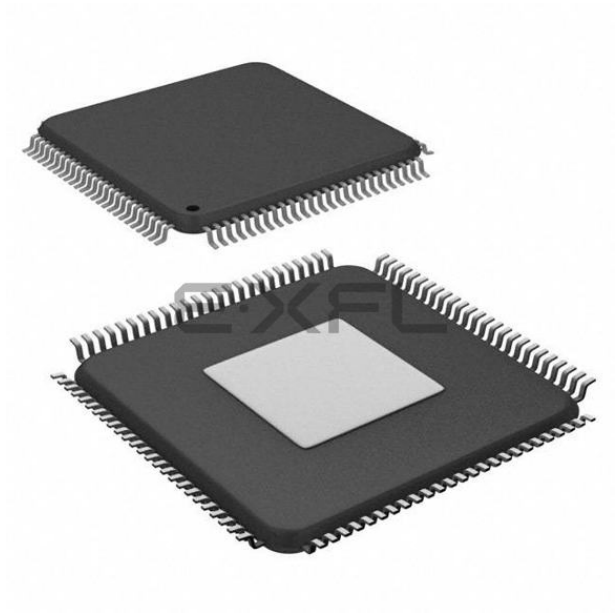
Infineon Technologies - XMC4402F64F256BAXQMA1 Datasheet



Welcome to E-XFL.COM

What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Active
Core Processor	ARM® Cortex®-M4
Core Size	32-Bit Single-Core
Speed	120MHz
Connectivity	CANbus, I²C, LINbus, SPI, UART/USART, USB
Peripherals	DMA, I²S, LED, POR, PWM, WDT
Number of I/O	31
Program Memory Size	256KB (256K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	80K x 8
Voltage - Supply (Vcc/Vdd)	3.13V ~ 3.63V
Data Converters	A/D 14x12b; D/A 2x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	100-LQFP Exposed Pad
Supplier Device Package	PG-LQFP-100-25
Purchase URL	https://www.e-xfl.com/product-detail/infineon-technologies/xmc4402f64f256baxqma1

2 General Device Information

This section summarizes the logic symbols and package pin configurations with a detailed list of the functional I/O mapping.

2.1 Logic Symbols

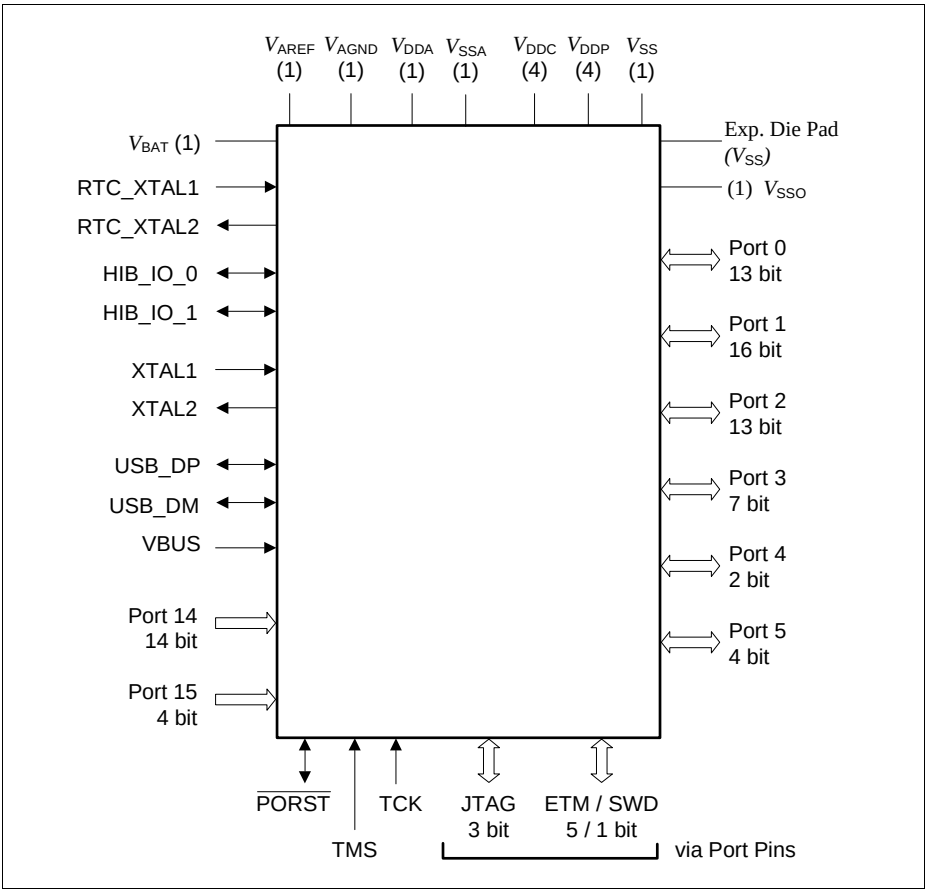


Figure 2 XMC4400 Logic Symbol PG-LQFP-100

2.2 Pin Configuration and Definition

The following figures summarize all pins, showing their locations on the different packages.

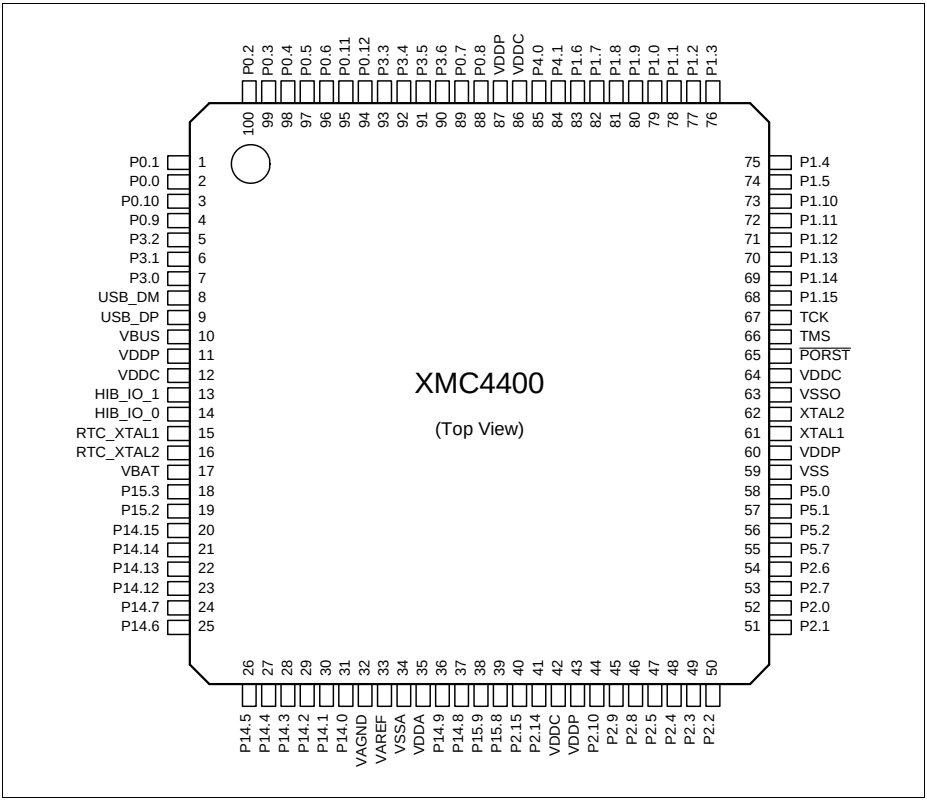


Figure 4 XMC4400 PG-LQFP-100 Pin Configuration (top view)

Table 10 Package Pin Mapping (cont'd)

Function	LQFP-100	LQFP-64 TQFP-64	Pad Type	Notes
VDDA/VAREF	-	22	AN_Power/AN_Ref	Shared analog supply and reference voltage pin.
VSSA	34	-	AN_Power	
VSSA/VAGND	-	21	AN_Power/AN_Ref	Shared analog supply and reference ground pin.
VDDC	12	9	Power	
VDDC	42	25	Power	
VDDC	64	42	Power	
VDDC	86	55	Power	
VDDP	11	8	Power	
VDDP	43	26	Power	
VDDP	60	38	Power	
VDDP	87	56	Power	
VSS	59	37	Power	
VSSO	63	41	Power	
VSS	Exp. Pad	Exp. Pad	Power	**Exposed Die Pad** The exposed die pad is connected internally to VSS. For proper operation, it is mandatory to connect the exposed pad directly to the common ground on the board. For thermal aspects, please refer to the Data Sheet. Board layout examples are given in an application note.

The XMC4400 has a common ground concept, all V_{SS}, V_{SSA} and V_{SSO} pins share the same ground potential. In packages with an exposed die pad it must be connected to the common ground as well.

V_{AGND} is the low potential to the analog reference V_{AREF}. Depending on the application it can share the common ground or have a different potential. In devices with shared V_{DDA}/V_{AREF} and V_{SSA}/V_{AGND} pins the reference is tied to the supply. Some analog channels can optionally serve as “Alternate Reference”; further details on this operating mode are described in the Reference Manual.

When V_{DDP} is supplied, V_{BAT} must be supplied as well. If no other supply source (e.g. battery) is connected to V_{BAT}, the V_{BAT} pin can also be connected directly to V_{DDP}.

3 Electrical Parameters

3.1 General Parameters

3.1.1 Parameter Interpretation

The parameters listed in this section partly represent the characteristics of the XMC4400 and partly its requirements on the system. To aid interpreting the parameters easily when evaluating them for a design, they are marked with an two-letter abbreviation in column “Symbol”:

- **CC**
  Such parameters indicate **C**ontroller **C**haracteristics, which are a distinctive feature of the XMC4400 and must be regarded for system design.
- **SR**
  Such parameters indicate **S**ystem **R**equirements, which must be provided by the application system in which the XMC4400 is designed in.

Figure 8 explains the input voltage ranges of V_{IN} and V_{AIN} and its dependency to the supply level of V_{DDP}.The input voltage must not exceed 4.3 V, and it must not be more than 1.0 V above V_{DDP}. For the range up to V_{DDP} + 1.0 V also see the definition of the overload conditions in **Section 3.1.3**.

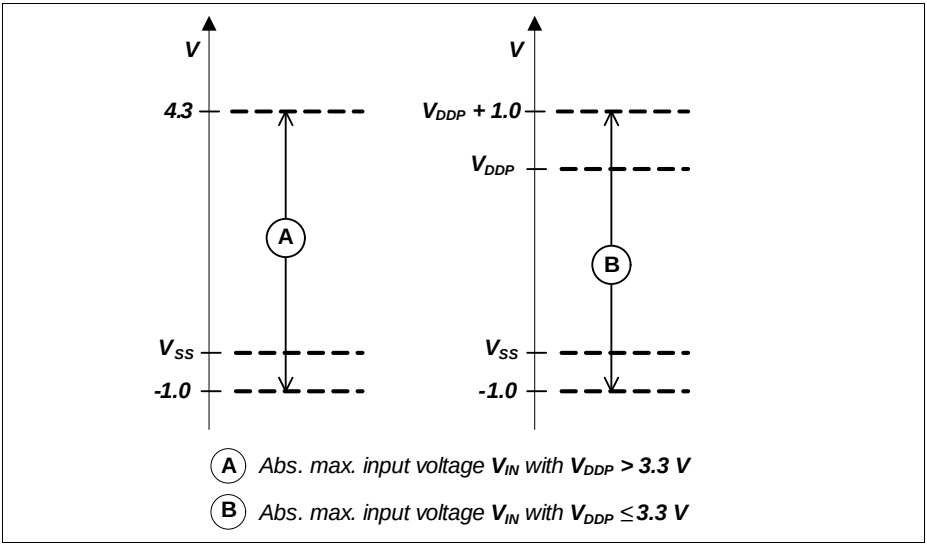


Figure 8 Absolute Maximum Input Voltage Ranges

3.1.3 Pin Reliability in Overload

When receiving signals from higher voltage devices, low-voltage devices experience overload currents and voltages that go beyond their own IO power supplies specification.

Table 14 defines overload conditions that will not cause any negative reliability impact if all the following conditions are met:

- full operation life-time is not exceeded
- **Operating Conditions** are met for
  - pad supply levels (V_{DDP} or V_{DDA})
  - temperature

If a pin current is outside of the **Operating Conditions** but within the overload parameters, then the parameters functionality of this pin as stated in the Operating Conditions can no longer be guaranteed. Operation is still possible in most cases but with relaxed parameters.

Note: An overload condition on one or more pins does not require a reset.

4) The sampling capacity of the conversion C-network is pre-charged to $V_{AREF}/2$ before the sampling moment. Because of the parasitic elements, the voltage measured at AINx can deviate from $V_{AREF}/2$.
5) Applies to AINx, when used as alternate reference input.
6) This represents an equivalent switched capacitance. This capacitance is not switched to the reference voltage at once. Instead, smaller capacitances are successively switched to the reference voltage.
7) For 10-bit conversions, the errors are reduced to 1/4; for 8-bit conversions, the errors are reduced to 1/16. Never less than ±1 LSB.
8) The sum of DNL/INL/GAIN/OFF errors does not exceed the related total unadjusted error TUE.
9) The resulting current for a conversion can be calculated with $I_{AREF} = Q_{CONV} / t_c$.
The fastest 12-bit post-calibrated conversion of t_c = 550 ns results in a typical average current of I_{AREF} = 54.5 µA.

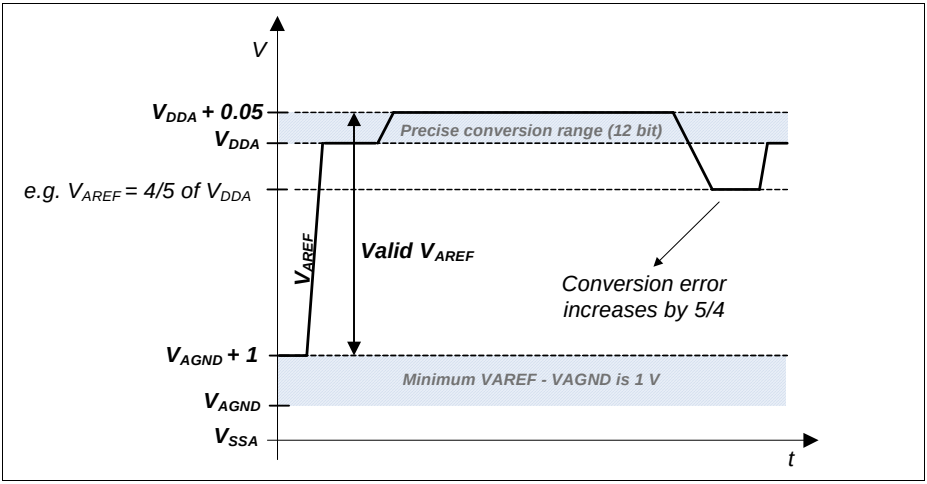


Figure 12 VADC Reference Voltage Range

The power-up calibration of the ADC requires a maximum number of 4 352 f_{ADCI} cycles.

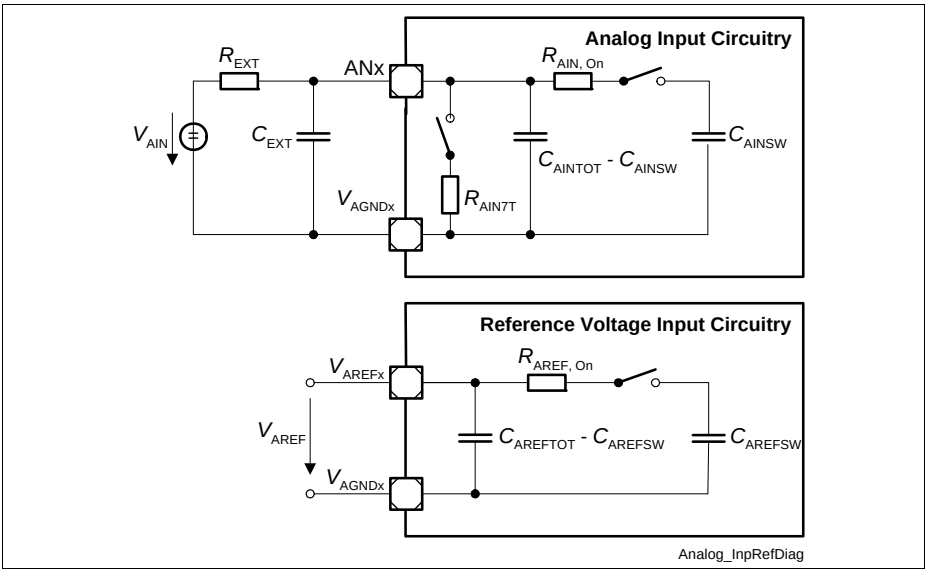


Figure 13 ADCx Input Circuits

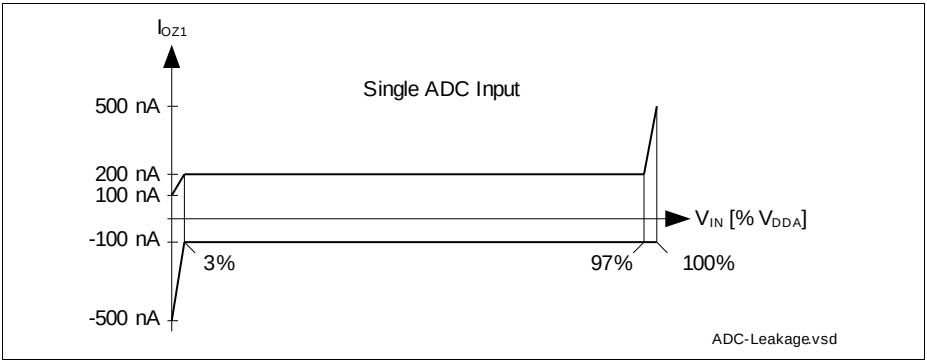


Figure 14 ADCx Analog Input Leakage Current

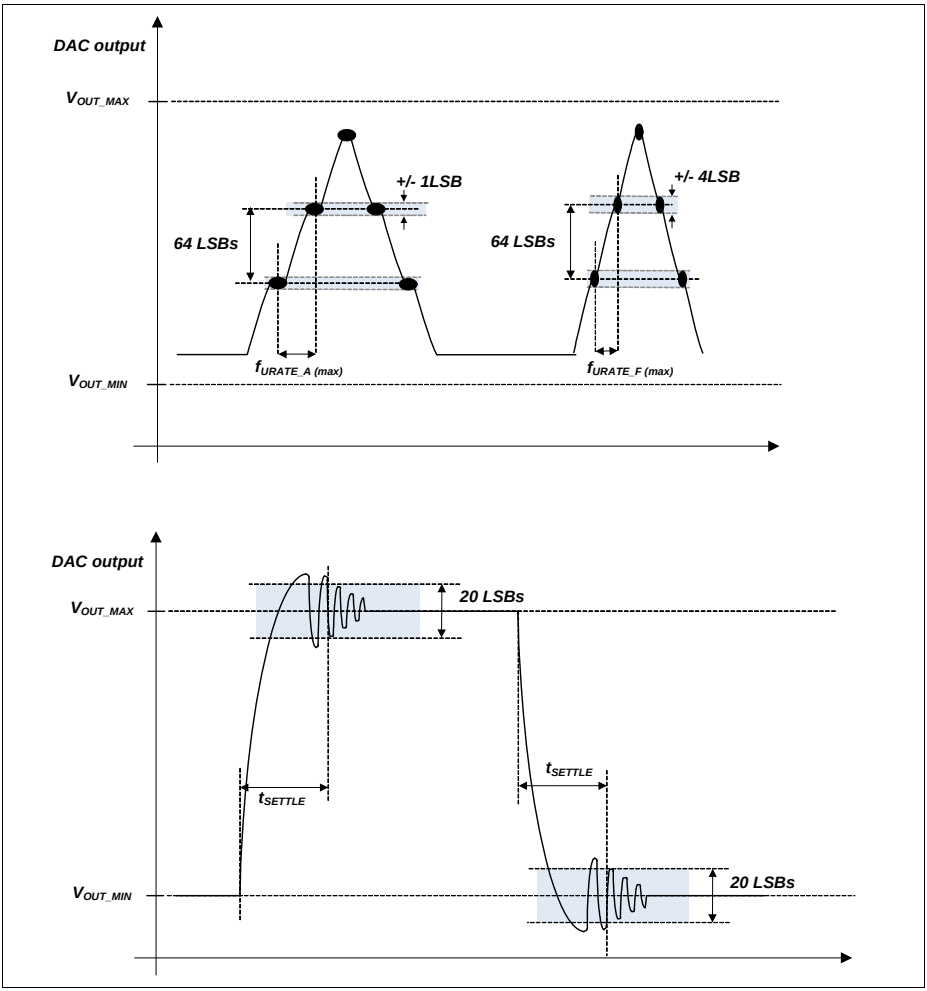


Figure 15 DAC Conversion Examples

Table 38 RTC_XTAL Parameters

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Input frequency	f_{OSC} SR	–	32.768	–	kHz	
Oscillator start-up time[1)2)3)]	t_{OSCS} CC	–	–	5	s	
Input voltage at RTC_XTAL1	V_{IX} SR	-0.3	–	V_{BAT} + 0.3	V	
Input amplitude (peak-to-peak) at RTC_XTAL1[2)4)]	V_{PPX} SR	0.4	–	–	V	
Input high voltage at RTC_XTAL1[5)]	V_{IHBX}SR	0.6 × V_{BAT}	–	V_{BAT} + 0.3	V	
Input low voltage at RTC_XTAL1[5)]	V_{ILBX} SR	-0.3	–	0.36 × V_{BAT}	V	
Input Hysteresis for RTC_XTAL1[5)6)]	V_{HYSX} CC	0.1 × V_{BAT}		–	V	3.0 V ≤ V_{BAT} < 3.6 V
		0.03 × V_{BAT}		–	V	V_{BAT} < 3.0 V
Input leakage current at RTC_XTAL1	I_{ILX1} CC	-100	–	100	nA	Oscillator power down 0 V ≤ V_{IX} ≤ V_{BAT}

1) t_{OSCS} is defined from the moment the oscillator is enabled by the user with SCU_OSCULCTRL.MODE until the oscillations reach an amplitude at RTC_XTAL1 of 400 mV.

2) The external oscillator circuitry must be optimized by the customer and checked for negative resistance and amplitude as recommended and specified by crystal suppliers.

3) For a reliable start of the oscillation in crystal mode it is required that $V_{BAT} \geq 3.0$ V. A running oscillation is maintained across the full V_{BAT} voltage range.

4) If the shaper unit is enabled and not bypassed.

5) If the shaper unit is bypassed, dedicated DC-thresholds have to be met.

6) Hysteresis is implemented to avoid metastable states and switching due to internal ground bounce. It can not be guaranteed that it suppresses switching due to external system noise.

3.3.2 Power-Up and Supply Monitoring

$\overline{\text{PORST}}$ is always asserted when V_{DDP} and/or V_{DDC} violate the respective thresholds.

Note: These parameters are not subject to production test, but verified by design and/or characterization.

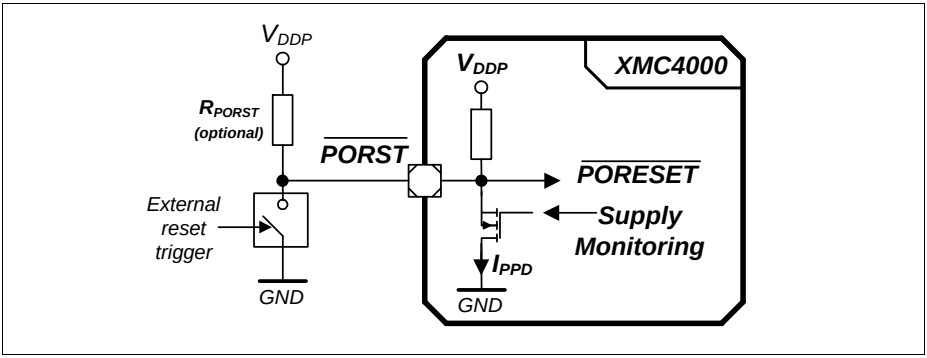


Figure 26 $\overline{\text{PORST}}$ Circuit

Table 42 Supply Monitoring Parameters

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Digital supply voltage reset threshold	V_{POR} CC	2.79[1]	–	3.05[2]	V	[3]
Core supply voltage reset threshold	V_{PV} CC	–	–	1.17	V	
V_{DDP} voltage to ensure defined pad states	V_{DDPPA} CC	–	1.0	–	V	
$\overline{\text{PORST}}$ rise time	t_{PR} SR	–	–	2	µs	
Startup time from power-on reset with code execution from Flash	t_{SSW} CC	–	2.5	3.5	ms	Time to the first user code instruction
V_{DDC} ramp up time	t_{VCR} CC	–	550	–	µs	Ramp up after power-on or after a reset triggered by a violation of V_{POR} or V_{PV}

1) Minimum threshold for reset assertion.

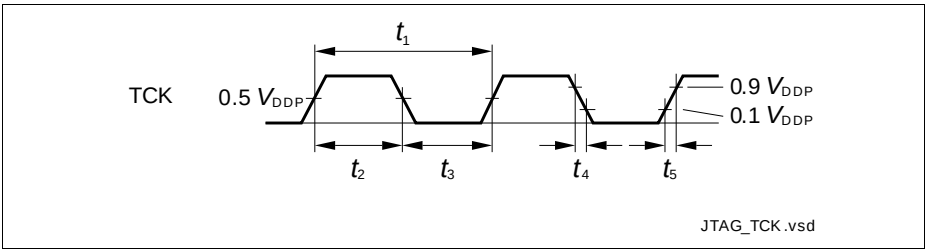


Figure 28 Test Clock Timing (TCK)

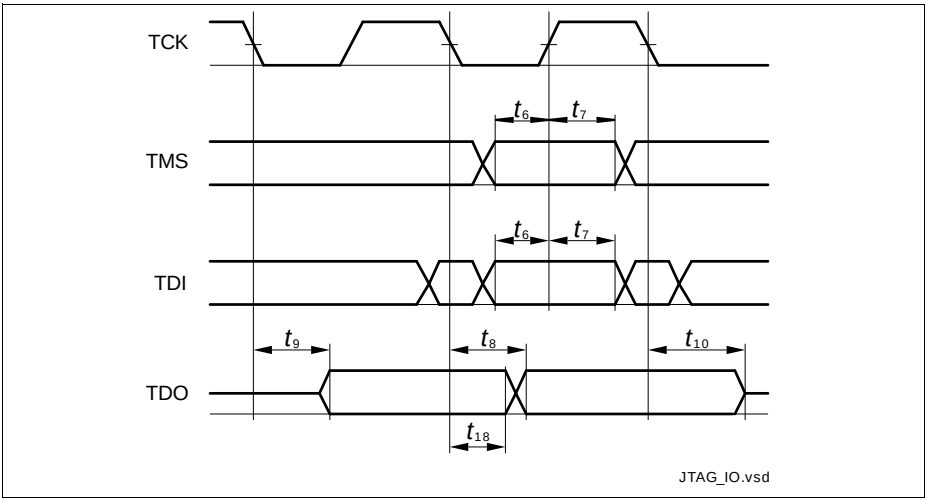


Figure 29 JTAG Timing

Table 52 USIC SSC Slave Mode Timing

Parameter	Symbol		Values			Unit	Note / Test Condition
			Min.	Typ.	Max.		
DX1 slave clock period	t_{CLK}	SR	66.6	–	–	ns	
Select input DX2 setup to first clock input DX1 transmit edge[1]	t_{10}	SR	3	–	–	ns	
Select input DX2 hold after last clock input DX1 receive edge[1]	t_{11}	SR	4	–	–	ns	
Receive data input DX0/DX[5:3] setup time to shift clock receive edge[1]	t_{12}	SR	6	–	–	ns	
Data input DX0/DX[5:3] hold time from clock input DX1 receive edge[1]	t_{13}	SR	4	–	–	ns	
Data output DOUT[3:0] valid time	t_{14}	CC	0	–	24	ns	

1) These input timing are valid for asynchronous input signal handling of slave select input, shift clock input, and receive data input (bits DXnCR.DSEN = 0).

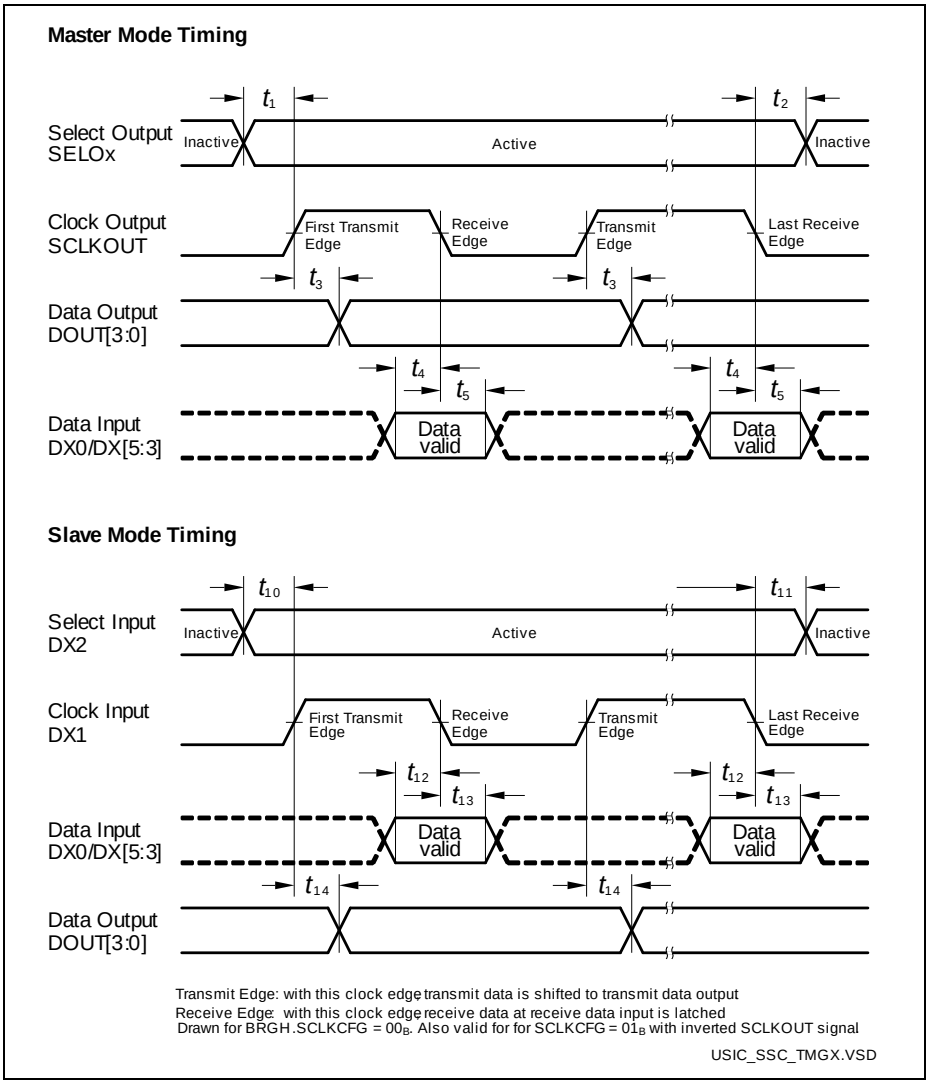


Figure 34 USIC - SSC Master/Slave Mode Timing

Note: This timing diagram shows a standard configuration, for which the slave select signal is low-active, and the serial clock signal is not shifted and not inverted.

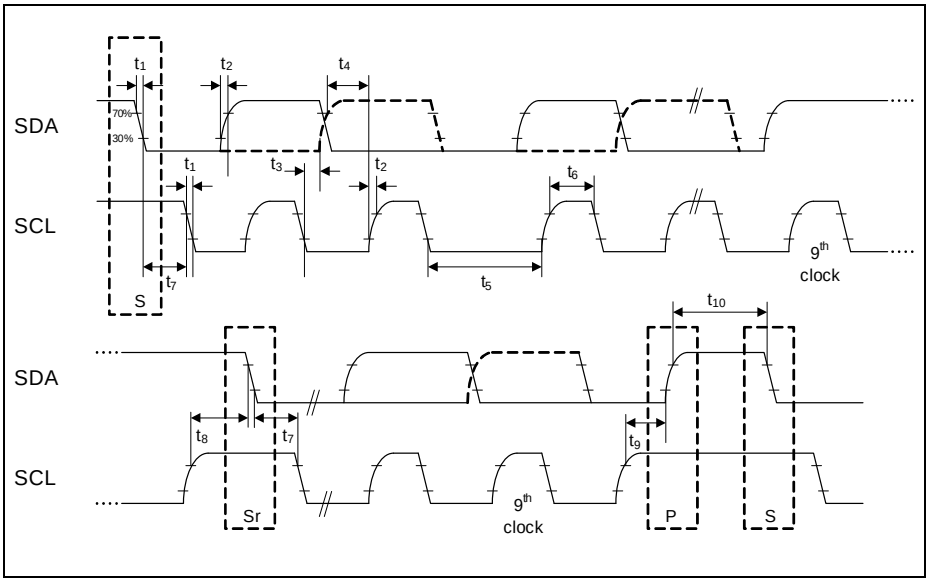


Figure 35 USIC IIC Stand and Fast Mode Timing

3.3.9.4 Inter-IC Sound (IIS) Interface Timing

The following parameters are applicable for a USIC channel operated in IIS mode.

Note: Operating Conditions apply.

Table 55 USIC IIS Master Transmitter Timing

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Clock period	t_1 CC	33.3	–	–	ns	
Clock HIGH	t_2 CC	0.35 x t_{1min}	–	–	ns	
Clock Low	t_3 CC	0.35 x t_{1min}	–	–	ns	
Hold time	t_4 CC	0	–	–	ns	
Clock rise time	t_5 CC	–	–	0.15 x t_{1min}	ns	

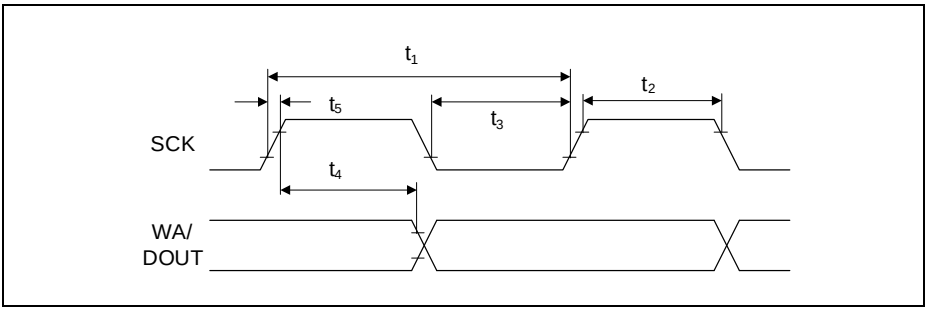


Figure 36 USIC IIS Master Transmitter Timing

Table 56 USIC IIS Slave Receiver Timing

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Clock period	t_6 SR	66.6	–	–	ns	
Clock HIGH	t_7 SR	0.35 x t_{6min}	–	–	ns	
Clock Low	t_8 SR	0.35 x t_{6min}	–	–	ns	
Set-up time	t_9 SR	0.2 x t_{6min}	–	–	ns	
Hold time	t_{10} SR	0	–	–	ns	

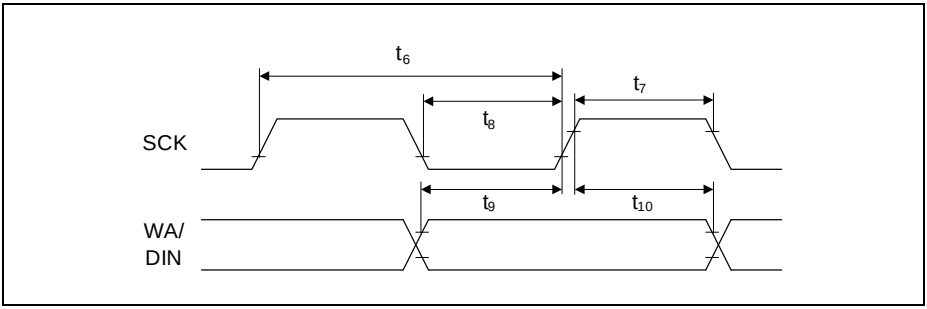


Figure 37 USIC IIS Slave Receiver Timing

3.3.10 USB Interface Characteristics

The Universal Serial Bus (USB) Interface is compliant to the USB Rev. 2.0 Specification and the OTG Specification Rev. 1.3. High-Speed Mode is not supported.

Note: These parameters are not subject to production test, but verified by design and/or characterization.

Table 57 USB Timing Parameters (operating conditions apply)

Parameter	Symbol		Values			Unit	Note / Test Condition
			Min.	Typ.	Max.		
Rise time	t_R	CC	4	–	20	ns	C_L = 50 pF
Fall time	t_F	CC	4	–	20	ns	C_L = 50 pF
Rise/Fall time matching	t_R/t_F	CC	90	–	111.11	%	C_L = 50 pF
Crossover voltage	V_{CRS}	CC	1.3	–	2.0	V	C_L = 50 pF

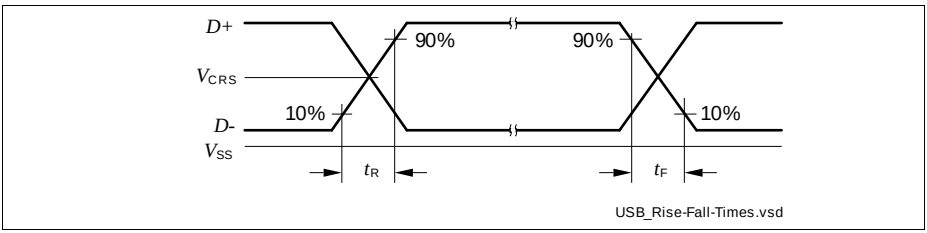


Figure 38 USB Signal Timing

3.3.11.3 ETH RMII Parameters

In the following, the parameters of the RMII (Reduced Media Independent Interface) are described.

Table 59 ETH RMII Signal Timing Parameters

Parameter	Symbol		Values			Unit	Note / Test Condition
			Min.	Typ.	Max.		
ETH_RMII_REF_CL clock period	t_{13}	SR	20	–	–	ns	C_L = 25 pF; 50 ppm
ETH_RMII_REF_CL clock high time	t_{14}	SR	7	–	13	ns	C_L = 25 pF
ETH_RMII_REF_CL clock low time	t_{15}	SR	7	–	13	ns	
ETH_RMII_RXD[1:0], ETH_RMII_CRS setup time	t_{16}	SR	4	–	–	ns	
ETH_RMII_RXD[1:0], ETH_RMII_CRS hold time	t_{17}	SR	2	–	–	ns	
ETH_RMII_TXD[1:0], ETH_RMII_TXEN data valid	t_{18}	CC	4	–	15	ns	

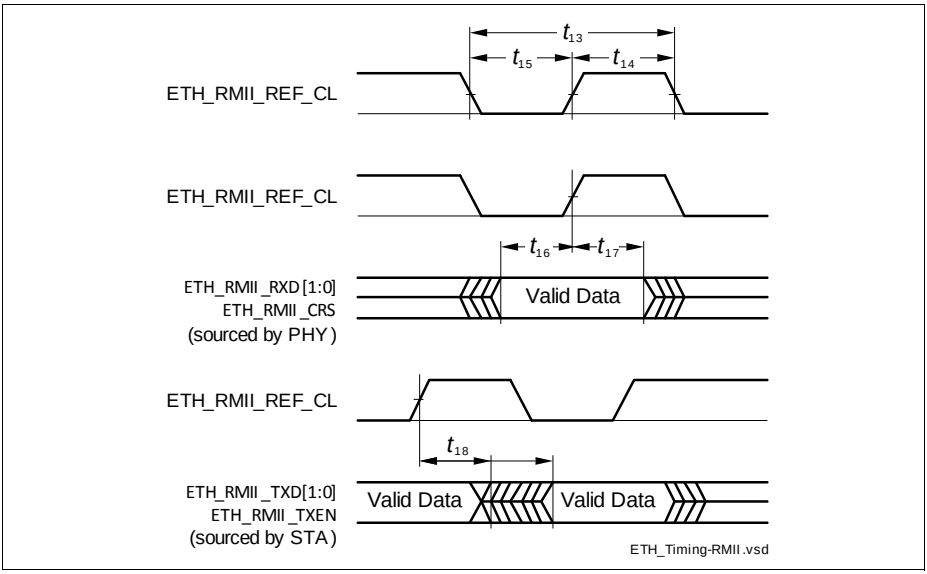


Figure 41 ETH RMII Signal Timing

The maximum heat that can be dissipated depends on the package and its integration into the target board. The “Thermal resistance $R_{\Theta JA}$” quantifies these parameters. The power dissipation must be limited so that the average junction temperature does not exceed 150 °C.

The difference between junction temperature and ambient temperature is determined by
$\Delta T = (P_{INT} + P_{IOSTAT} + P_{IODYN}) \times R_{\Theta JA}$

The internal power consumption is defined as
$P_{INT} = V_{DDP} \times I_{DDP}$ (switching current and leakage current).

The static external power consumption caused by the output drivers is defined as
$P_{IOSTAT} = \Sigma((V_{DDP}-V_{OH}) \times I_{OH}) + \Sigma(V_{OL} \times I_{OL})$

The dynamic external power consumption caused by the output drivers (P_{IODYN}) depends on the capacitive load connected to the respective pins and their switching frequencies.

If the total power dissipation for a given system configuration exceeds the defined limit, countermeasures must be taken to ensure proper system operation:

- Reduce V_{DDP}, if possible in the system
- Reduce the system frequency
- Reduce the number of output pins
- Reduce the load on active output drivers

4.2 Package Outlines

The availability of different packages for different devices types is listed in **Table 1**, specific packages for different device markings are listed in **Table 2**.

The exposed die pad dimensions are listed in **Table 60**.

Table 61 Differences PG-LQFP-100-11 to PG-LQFP-100-24

Change	PG-LQFP-100-11	PG-LQFP-100-25
Thermal Resistance Junction Ambient ($R_{\Theta JA}$)	20.5 K/W	20.0 K/W
Lead Width	$0.22^{\pm 0.05}$ mm	$0.2^{+0.07}_{-0.03}$ mm
Lead Thickness	$0.15^{+0.05}_{-0.06}$ mm	$0.127^{+0.073}_{-0.037}$ mm
Exposed Die Pad outer dimensions	7.0 mm × 7.0 mm	7.0 mm × 7.0 mm
Exposed Die Pad U-Groove inner dimensions	n.a.	6.2 mm × 6.2 mm

Table 62 Differences PG-LQFP-64-19 to PG-TQFP-64-19

Change	PG-LQFP-64-19	PG-TQFP-64-19
Thermal Resistance Junction Ambient ($R_{\Theta JA}$)	30.0 K/W	22.5 K/W
Package thickness	$1.4^{\pm 0.05}$ mm	$1.0^{\pm 0.05}$ mm
	1.6 mm MAX	1.2 mm MAX
Lead Width	$0.22^{\pm 0.05}$ mm	$0.2^{+0.07}_{-0.03}$ mm
Lead Thickness	$0.15^{+0.05}_{-0.06}$ mm	$0.127^{+0.07}_{-0.04}$ mm
Exposed Die Pad outer dimensions	5.8 mm × 5.8 mm	5.7 mm × 5.7 mm
Exposed Die Pad U-Groove inner dimensions	n.a.	4.9 mm × 4.9 mm

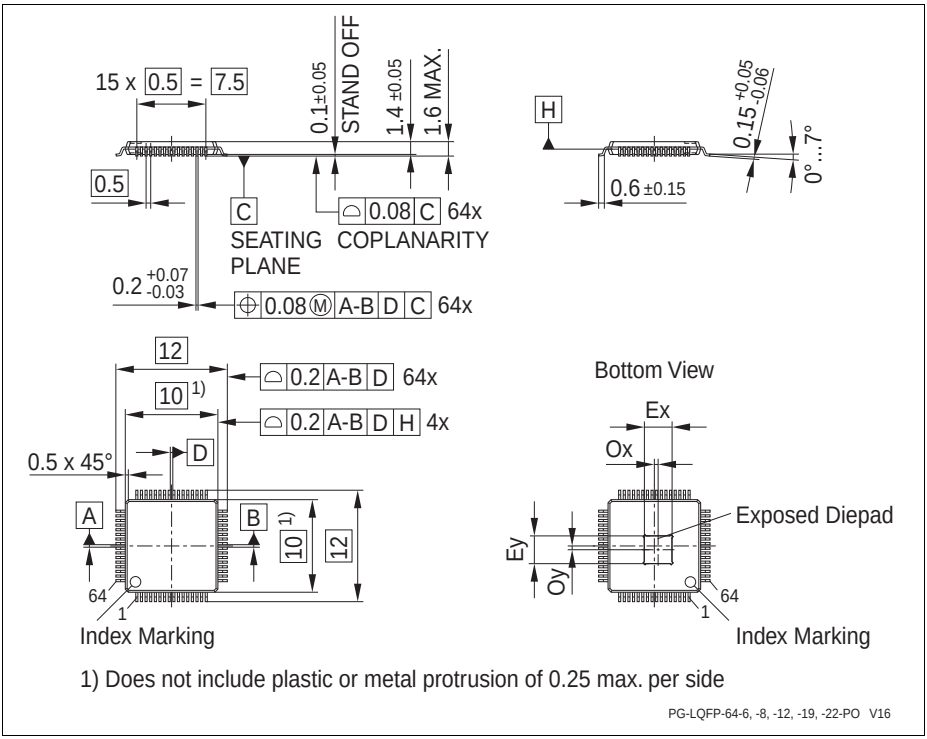


Figure 44 PG-LQFP-64-19 (Plastic Green Low Profile Quad Flat Package)